MALLA REDDY COLLEGE OF ENGINEERING & TECHNOLOGY (Autonomous Institution – UGC, Govt. of India) **UG Model question paper Engineering Physics**

SECTION-I	
1 a) Discuss the theory of Newton's rings with necessary diagram	[10M]
b) Write the difference between interference and diffraction.	[4M]
OR	
2 a) Derive the expression for bright and dark fringes when the interference pattern is for	orm in
thin films due to reflected light.	[8M]
b) Explain the concept of double refraction.	[6M]
SECTION-II	
3 a) Explain the construction and working principle of He - Ne laser with neat diagram.	[8M]
b) Write the applications of laser.	[6M]
OR	L - J
4 a) Derive the expression for numerical aperture and acceptance angle.	[10M]
b) Write the advantages of an optical fiber.	[4M]
SECTION-III	
5 a) Show that energy levels in 1D potential box are descrete.	[10]
b) Define particle and wave nature of light.	[4M]
OR	
6 a) Explain the G.P. Thomson experiment that verify the wave nature of light.	[10M]
b) An electron is moving under a potential field of 15 kV. Calculate the wavelength of e	lectron
waves.	[4M]
SECTION-IV	
7 a) Distinguish between Fermi dirac distribution and Bose Einstein distribution.	[8M]
b) Explain the orgin of energy bands in solids.	[6M]
OR	
8 a) Show that the Kronig Penny modes leads to energy band structure in solids.	[10M]
b) Explain E – K diagram.	[4M]
SECTION-V	
9 a) Derive an expression for concentration of electrons in intrinsic semiconductor.	[8M]
b) Write short notes on LED.	[6M]
OR	
10 a) Define hall effect and derive an expression for hall coefficient for P – type semicono	ductor.
	[8M]
b) Explain construction and working of solar cell.	[6M]

Note: This question paper contains of 5 sections. Answer five questions, choosing one question from each section and each question carries 14 marks.

Max Marks: 70

Time: 3 hours

CECTION I

MALLA REDDY COLLEGE OF ENGINEERING & TECHNOLOGY (Autonomous Institution – UGC, Govt. of India) UG Model question paper Engineering Physics

Time: 3 hours

Max Marks: 70

Note: This question paper contains of 5 sections. Answer five questions, choosing one question from each section and each question carries 14 marks.

SECTION-I

1	a) Derive the expression for bright and dark fringes in thin film due to reflected ray	[10M]
	b) Define and explain the coherent sources	[4M]
~	OR LAND CARE AND A LAND A	
2	a) Explain the formation of Newton's rings and write applications of newton's ring experiment.	[10M]
	b) In Newton's ring experiment the diameter of 7 th dark ring is 3.3mm. Then calculate	the
	diameter of 10^{th} ring if the wavelength of monochromatic light used is 2000 A° . SECTION-II	[4M]
3	a) Derive the relation between Einstein's coefficients	[8M]
	b) Write short notes on population inversion	[6M]
	OR	
4	a) Define and Derive the expression for numerical aperture and acceptance angle of an fiber	optical [10M]
	b) For an optical fiber the refractive indices of core and clad are 1.50 and 1.41 then det numerical aperture and acceptance angle of the optical fiber assuming that light is la into optical fiber from air medium	ermine unched [4M]
	SECTION-III	[]
5	a) Derive the time independent Schrödinger's wave equation.	[8M]
	b) Write a short notes on Heisenberg's uncertainty principle OR	[6M]
6	a) Show that the wavelength λ associated with a electron of mass m is given by $\lambda = \frac{h}{\sqrt{2mE}}$	[10M]
	b) Electrons are accelerated by 340 V and reflected from a crystal in the first order diffr	action
	when the angle of incidence is 60°. Then calculate inter planar distance. SECTION-IV	[4M]
7	a) Explain about MB & Fermi dirac distribution and Bose Einstein distribution.	[8M]
	b) Explain the orgin of energy bands in solids.	[6M]
	OR	
8	a) Write a short notes an Brillouin zones	[10M]
	b) Define and derive the expression for effective mass.	[4M]
	SECTION-V	
9	a) Derive an expression for concentration of electrons in intrinsic semiconductor.	[8M]
	b) Distinguish direct and indirect band gap semiconductors	[6M]
	OR	
1(0 a) What is hall effect ? And derive expression for hall coefficient?	[10M]
	b) The hall coefficient of a specimen is $7.35 \times 10^{-5} m^3/cm$. Then find the nature of	500
	semiconductor and concentration of charge carriers.	[6M]

MALLA REDDY COLLEGE OF ENGINEERING & TECHNOLOGY (Autonomous Institution - UGC, Govt. of India) **UG Model question paper Engineering Physics**

from each section and each question carries 14 marks. **SECTION-I** 1 a) Derive the conditions for bright and dark fringes in thin film due to reflected ray. [10M] b) Write the difference between Fresnel and fraunhoffer diffraction. [4M] OR 2 a) Derive the conditions for bright and dark fringes in fraunhoffer diffraction due to single slit. [8M] b) Explain the construction and working of NIcol prism. [6M] **SECTION-II** 3 a) Explain the construction and working principle of Ruby laser with neat diagram. [8M] b) Explain the characteristics of laser. [6M] OR 4 a) Explain the transmission of light in optical fiber communication system with a suitable block diagram [10M] b) Explain the working principle of optical fiber. [4M] **SECTION-III** 5 a) Write the properties of matter waves. [4M] b) Derive the time independent schrodinger wave equation. [10M] OR 6 a) Explain the Davisson and Germer experiment that verify the wave nature of light. [10M] b) Calculate the wavelength of an electron associated with an energy of 2000 e V. [4M] **SECTION-IV** 7 a) Derive the expression for density of states. [8M] b) Write short notes on Brillouin zones. [6M] OR 8 a) Explain about MB, BE statistics. [6M] b) Define and derive the expression for effective mass of an electron. [10M] **SECTION-V** 9 a) Derive an expression for concentration of holes in intrinsic semiconductor. [10M] b) Write advantages of hall effect. [4M] OR 10 a) Distinguish between direct and indirect band gap semiconductors. [6M]

b) Explain construction and working of solar cell. [8M]

Time: 3 hours **Note:** This question paper contains of 5 sections. Answer five questions, choosing one question

Max Marks: 70

MALLA REDDY COLLEGE OF ENGINEERING & TECHNOLOGY (Autonomous Institution - UGC, Govt. of India) **UG Model question paper Engineering Physics**

	Time: 3 hours Max Marks: 70	0
	Note: This question paper contains of 5 sections. Answer five questions, choosing one	
	question from each section and each question carries 14 marks.	
	SECTION-I	
	1 a) Explain in detail interference in thin films by reflected light?	[7 M]
	b) Derive an expression for wavelength of light by forming Newton rings? OR	[7 M]
	2 a) Describe and explain the phenomenon of diffraction due to a single slit. Determine	the
	positions of principle maxima and minima?	[10 M]
	b) In Newton's Rings experiment, diameter of 10 th dark ring due to wavelength 6000	Aº in
	air is 0.5cm. Find the radius of curvature of lens?	[4 M]
	SECTION-II	
	3 a) Explain the terms:	
	i.Stimulated emission ii.Population Inversion	
	iii. Meta stable state iv. Optical Pumping	[4 M]
	b) Explain the construction and working of He- Ne laser with the help of energy level	[40] []
	diagram?	[10M]
	UR	[7] 1/1
	4 a) write a note on types of optical fiber with propagation of light through it?	
	b) Explain attenuation in fibers?	[4 M]
		[3 M]
	SECTION-III 5. a) Evalain De Broglie concent of matter wayee?	[5M]
	b) What are matter waves? Describe the experiment that supports the existence of ma	[JM]
	waves?	[7M]
	c) Write the statement of Heisenberg Uncertainty principle?	[7 M]
	OR	[21.1]
	6 a) Derive the Eigen value and Eigen function for a particle in a potential box?	[7M]
	b) Derive Schrödinger time independent wave equation?	[7M]
	SECTION-IV	[]
	7 a) Distinguish MB, BE, FD statistical distribution?	[7M]
	b) Derive an expression for the density of energy states?	[7M]
	OR	
	8 a) Explain the Kronig Penny model of solids and show that it leads to energy band stru	ucture
	of solids?	[7M]
	b) Obtain an expression for the Fermi energy in metals at T=0K?	[7M]
	SECTION-V	
	9 a) Calculate the carrier concentration in N-Type semiconductor?	[7M]
	b) What is Hall Effect and Derive an expressions for hall voltage and hall coefficient?	[5M]
	c) Mention important applications of Hall effect?	[5M]
	OR	_
10	a) Derive an expression for Fermi energy in intrinsic semi conductor. What is the effect	of
	temperature on Fermi level in intrinsic semi conductor?	[7M]
	b)Write short notes on: solar cell and LED	[7M]

MALLA REDDY COLLEGE OF ENsssssGINEERING & TECHNOLOGY (Autonomous Institution – UGC, Govt. of India) UG Model question paper Engineering Physics

N	ote: This question paper contains of 5 sections. Answer five questions, choosing one question from each section and each question carries 14 marks.	
	SECTION-I	
1	a) Show that fringe-width is same for bright fringe and dark fringes in interference of light?	[7M]
	b) Derive an expressions for diameters of bright and dark rings in Newton's rings ? OR	[7M]
2	a) Describe Fraunhofer diffraction due to single slit & discuss intensity-curve of	
	diffraction?	[10M]
	b) In Newton's Rings experiment, diameter of 5 th dark ring is 0.30 cm and the diameter the 15th ring is 0.62 cm. Find the diameter of the 25 th ring. SECTION-II	er of [4M]
3	a) Derive the relation between the probabilities of spontaneous and stimulated emiss	sion
-	in terms of Einstein's coefficients.	[7M]
	b) Explain the construction and working of GaAs laser? OR	
4	a) Derive expressions for the numerical aperture and the fractional change of an opti	cal
	fiber	[7M]
	 b) Explain different types of fibers by giving the refractive index profiles and propaga details. 	ation [7M]
	SECTION-III	
5	a) Derive time-independent Schrodinger's wave equation for a free particle ?b) What are matter waves? Describe the experiment that supports the existence of matching of the existence of the exis	[7M] itter
	waves?	[7M]
6	a) Show that the energy levels of the particle are quantized?	[7M]
U	b) State Heisenberg uncertainity principle? Explain the physical significance of the wa	ave-
	function of the particle	[7M]
	SECTION-IV	
7	a) Distinguish MB, BE, FD statistical distribution?	[7M]
	b) Derive an expression for the density of energy states?	[7M]
~	OR	
8	a) Explain the Kronig Penny model of solids and show that it leads to energy band stru of solids?	icture [7M]
	b) Obtain an expression for the Fermi energy in metals at T=0K? SECTION-V	[7M]
9	a) Calculate the carrier concentration in P-Type semiconductor?	[7M]
	b) What is Hall Effect and Derive an expressions for hall voltage and hall coefficient? c) Mention important applications of Hall effect?	[5M] [2M]
	OR	
1	0 a) Derive an expression for Fermi energy in intrinsic semi conductor. What is the effect temperature on Fermi level in intrinsic semi conductor?	ect of [7M]
	b)Write short notes on: solar cell and LED?	[7M]

Time: 3 hours

Max Marks: 70